

# Xuwei Feng

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/3096235/publications.pdf>

Version: 2024-02-01

30  
papers

1,410  
citations

393982

19  
h-index

642321

23  
g-index

30  
all docs

30  
docs citations

30  
times ranked

2059  
citing authors

#	ARTICLE	IF	CITATIONS
1	Artificial Synapses Based on Multiterminal Memtransistors for Neuromorphic Application. <i>Advanced Functional Materials</i> , 2019, 29, 1901106.	7.8	192
2	2D Photovoltaic Devices: Progress and Prospects. <i>Small Methods</i> , 2018, 2, 1700294.	4.6	135
3	Few-layer Black Phosphorus Carbide Field-Effect Transistor via Carbon Doping. <i>Advanced Materials</i> , 2017, 29, 1700503.	11.1	133
4	A Fully Printed Flexible MoS <sub>2</sub> Memristive Artificial Synapse with Femtojoule Switching Energy. <i>Advanced Electronic Materials</i> , 2019, 5, 1900740.	2.6	123
5	Impact and Origin of Interface States in MOS Capacitor with Monolayer MoS <sub>2</sub> and HfO <sub>2</sub> High-k Dielectric. <i>Scientific Reports</i> , 2017, 7, 40669.	1.6	83
6	Self-Selective Multi-Terminal Memtransistor Crossbar Array for In-Memory Computing. <i>ACS Nano</i> , 2021, 15, 1764-1774.	7.3	80
7	High Mobility Anisotropic Black Phosphorus Nanoribbon Field-Effect Transistor. <i>Advanced Functional Materials</i> , 2018, 28, 1801524.	7.8	77
8	Electron-beam-irradiated rhenium disulfide memristors with low variability for neuromorphic computing. <i>Npj 2D Materials and Applications</i> , 2021, 5, .	3.9	69
9	A van der Waals Synaptic Transistor Based on Ferroelectric Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> and 2D Tungsten Disulfide. <i>Advanced Electronic Materials</i> , 2020, 6, 2000057.	2.6	68
10	Black Phosphorus Carbide as a Tunable Anisotropic Plasmonic Metasurface. <i>ACS Photonics</i> , 2018, 5, 3116-3123.	3.2	58
11	An Electronic Synapse Based on 2D Ferroelectric CuInP <sub>2</sub> S <sub>6</sub> . <i>Advanced Electronic Materials</i> , 2020, 6, 2000760.	2.6	57
12	2D photonic memristor beyond graphene: progress and prospects. <i>Nanophotonics</i> , 2020, 9, 1579-1599.	2.9	54
13	Black Phosphorus Based Field Effect Transistors with Simultaneously Achieved Near Ideal Subthreshold Swing and High Hole Mobility at Room Temperature. <i>Scientific Reports</i> , 2016, 6, 24920.	1.6	35
14	Efficient and reliable surface charge transfer doping of black phosphorus <i>via</i> atomic layer deposited MgO toward high performance complementary circuits. <i>Nanoscale</i> , 2018, 10, 17007-17014.	2.8	34
15	Anomalously enhanced thermal stability of phosphorene via metal adatom doping: An experimental and first-principles study. <i>Nano Research</i> , 2016, 9, 2687-2695.	5.8	33
16	Recent Advances in Black Phosphorus-Based Electronic Devices. <i>Advanced Electronic Materials</i> , 2019, 5, 1800666.	2.6	31
17	Pronounced Photovoltaic Effect in Electrically Tunable Lateral Black-Phosphorus Heterojunction Diode. <i>Advanced Electronic Materials</i> , 2018, 4, 1700442.	2.6	27
18	Tunable black phosphorus heterojunction transistors for multifunctional optoelectronics. <i>Nanoscale</i> , 2018, 10, 14359-14367.	2.8	24

#	ARTICLE	IF	CITATIONS
19	Gigahertz Integrated Circuits Based on Complementary Black Phosphorus Transistors. <i>Advanced Electronic Materials</i> , 2018, 4, 1800274.	2.6	23
20	Aerosol Jet Printed WSe <sub>2</sub> Crossbar Architecture Device on Kapton With Dual Functionality as Resistive Memory and Photosensor for Flexible System Integration. <i>IEEE Sensors Journal</i> , 2020, 20, 4653-4659.	2.4	15
21	Complementary Black Phosphorus Nanoribbons Field-Effect Transistors and Circuits. <i>IEEE Transactions on Electron Devices</i> , 2018, 65, 4122-4128.	1.6	14
22	A unified surface potential based physical compact model for both unipolar and ambipolar 2D-FET: Experimental verification and circuit demonstration. , 2017, , .		10
23	First Demonstration of a Fully-Printed Mos2Rram on Flexible Substrate with Ultra-Low Switching Voltage and its Application as Electronic Synapse. , 2019, , .		8
24	Black phosphorus transistors with enhanced hole transport and subthreshold swing using ultra-thin HfO <sub>2</sub> /high-k gate dielectric. , 2016, , .		7
25	A surface potential based compact model for two-dimensional field effect transistors with disorders induced transition behaviors. <i>Journal of Applied Physics</i> , 2018, 124, .	1.1	6
26	Aerosol Jet Printed WSe <sub>2</sub> Based RRAM on Kapton Suitable for Flexible Monolithic Memory Integration. , 2019, , .		6
27	Ultrasensitive Flexible Strain Sensor based on Two-Dimensional InSe for Human Motion Surveillance. , 2019, , .		3
28	Recent advances in black phosphorus and transition metal dichalcogenide-based electronic and optoelectronics devices. , 2020, , 251-312.		3
29	Charge Carrier Mobility and Series Resistance Extraction in 2D Field-Effect Transistors: Toward the Universal Technique. <i>Advanced Functional Materials</i> , 2021, 31, 2105003.	7.8	2
30	Gradual Resistive Switching in Electron Beam Irradiated ReS <sub>2</sub> Transistor and its Application as Electronic Synapse. , 2020, , .		0